



## Description

### JMP N-channel MOSFET

#### Features

- 650V, 10A
- $R_{DS(ON)} = 0.95\Omega$  (Typ.) @  $V_{GS} = 10V$ ,  $I_D = 5A$
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

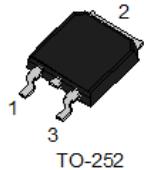
#### Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)

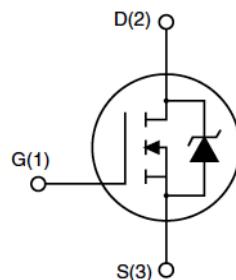
#### Package



JMPF10N65C



JMPK10N65C



### Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.		Units
		TO-220F	TO-252	
$V_{DSS}$	Drain-Source Voltage	650		V
$V_{GSS}$	Gate-Source Voltage	$\pm 30$		V
$I_D$	Continuous Drain Current $T_C = 25^\circ C$	10		A
		$T_C = 100^\circ C$	6.5	A
$I_{DM}$	Pulsed Drain Current <sup>note1</sup>	40		A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>note2</sup>	720		mJ
$P_D$	Power Dissipation $T_C = 25^\circ C$	64	123	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.95	1.02	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	62.5	$^\circ C/W$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		°C

**Electrical Characteristics** ( $T_C=25^\circ\text{C}$  unless otherwise specified)

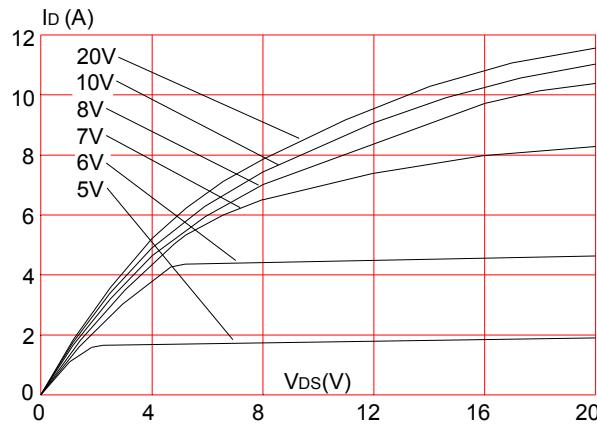
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu\text{A}$	650	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=650V, V_{GS}=0V, T_J=25^\circ\text{C}$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm30V$	-	-	$\pm100$	nA
<b>On Characteristics</b>						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2	-	4	V
$R_{DS(\text{on})}$	Static Drain-Source on-Resistance note3	$V_{GS}=10V, I_D=5\text{A}$	-	0.95	1.15	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1.0\text{MHz}$	-	1100	-	pF
$C_{oss}$	Output Capacitance		-	126	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	19	-	pF
$Q_g$	Total Gate Charge	$V_{DD}=520V, I_D=10\text{A}, V_{GS}=10V$	-	32	-	nC
$Q_{gs}$	Gate-Source Charge		-	5	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	16	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=325V, I_D=10\text{A}, R_G=25\Omega$	-	23	-	ns
$t_r$	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	90	-	ns
$t_f$	Turn-off Fall Time		-	30	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_s$	Maximum Continuous Drain to Source Diode Forward Current	-	-	9	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	36	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_{SD}=10\text{A}$	-	-	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS}=0V, I_s=10\text{A}, \text{di}/\text{dt}=100\text{A}/\mu\text{s}$	-	310	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	4.1	-	$\mu\text{C}$

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

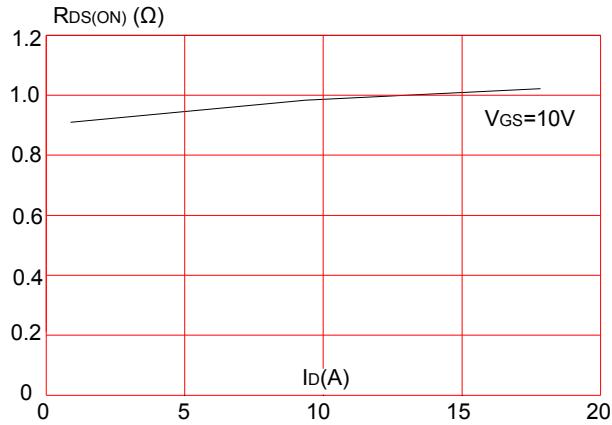
2.  $I_{AS}=7\text{A}, V_{DD}=50V, R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$ 3. Pulse Test: Pulse Width $\leq 325\mu\text{s}$ , Duty Cycle $\leq 1\%$

## Typical Performance Characteristics

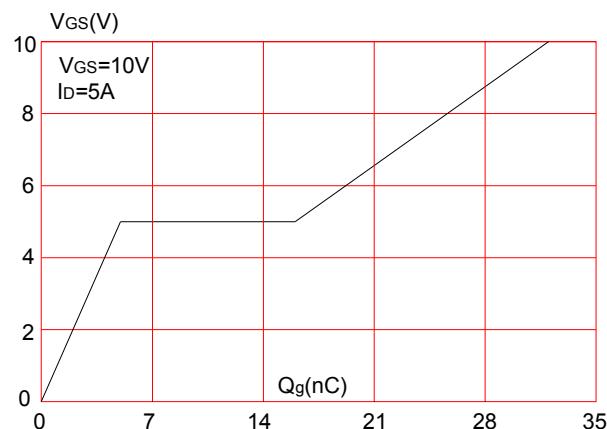
**Figure1:** Output Characteristics



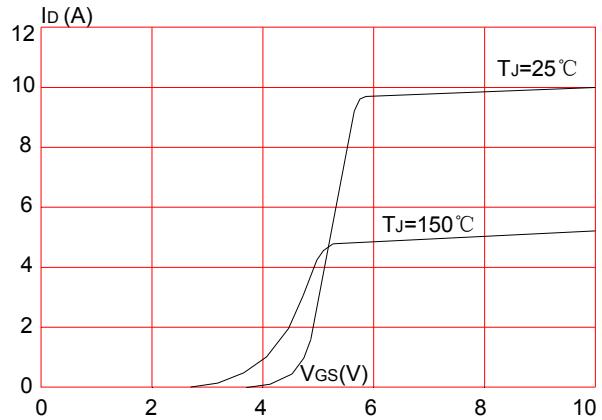
**Figure 3:** On-resistance vs. Drain Current



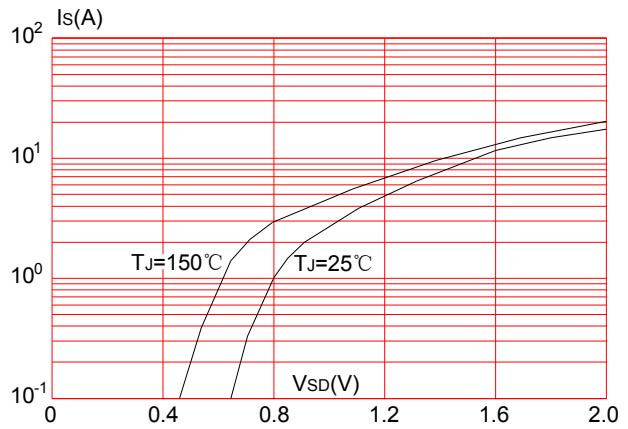
**Figure 5:** Gate Charge Characteristics



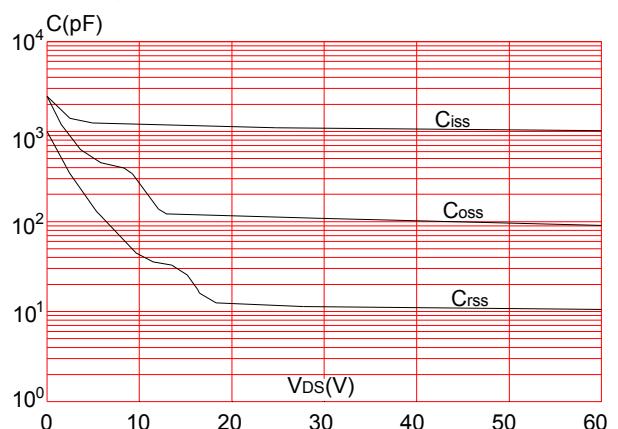
**Figure 2:** Typical Transfer Characteristics



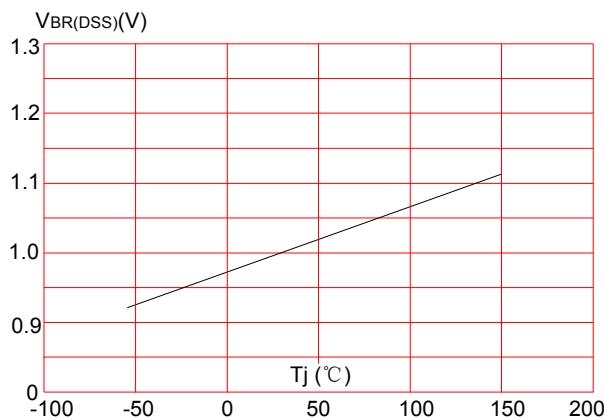
**Figure 4:** Body Diode Characteristics



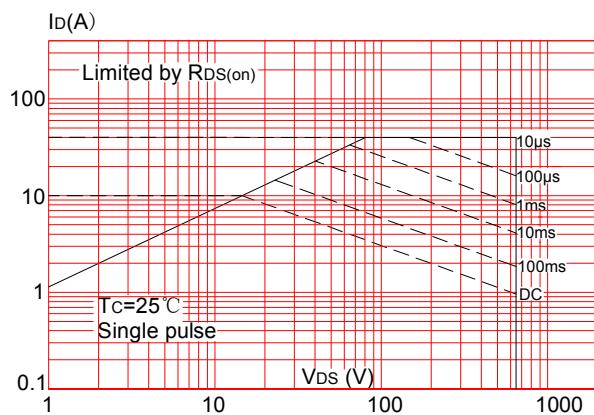
**Figure 6:** Capacitance Characteristics



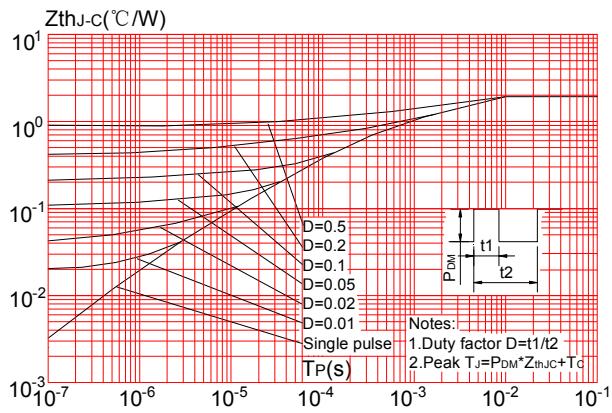
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



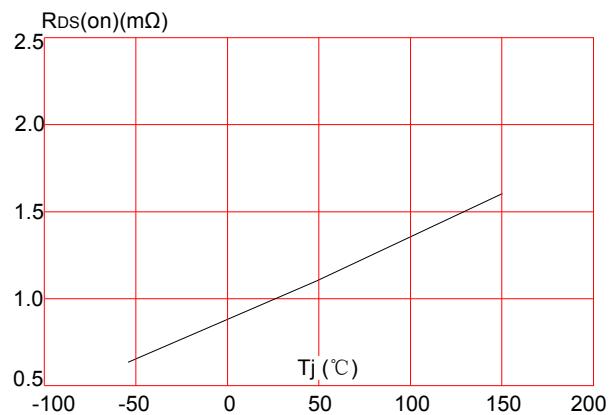
**Figure 9:** Maximum Safe Operating Area



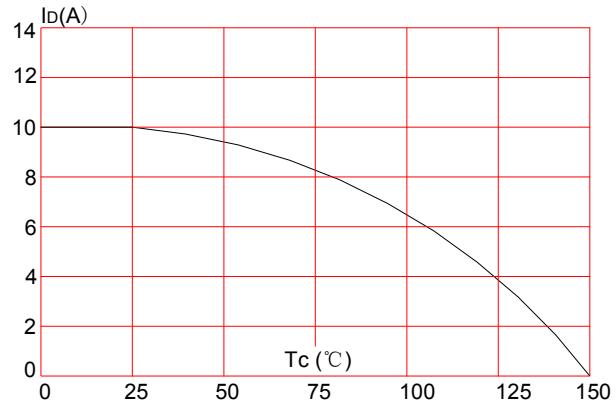
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220F)



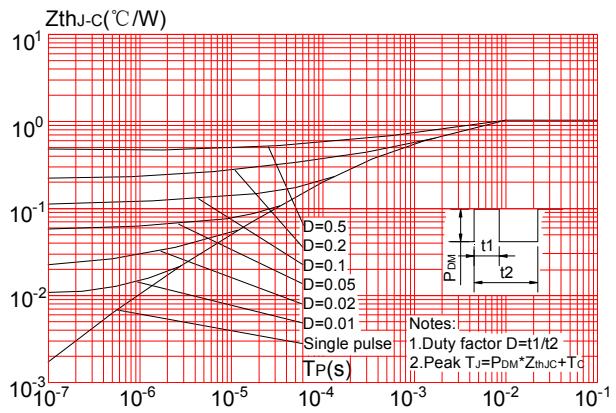
**Figure 8:** Normalized on Resistance vs. Junction Temperature

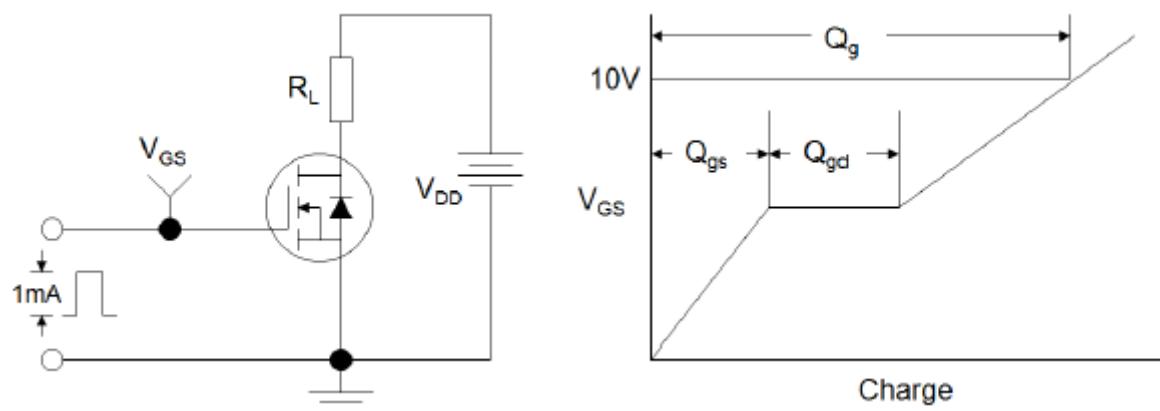


**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

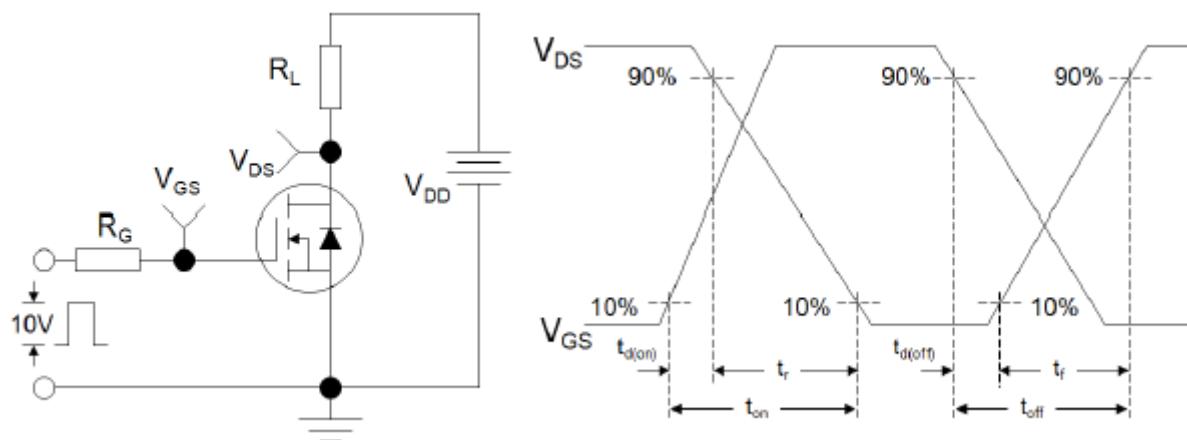


**Figure.12:** Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-252)

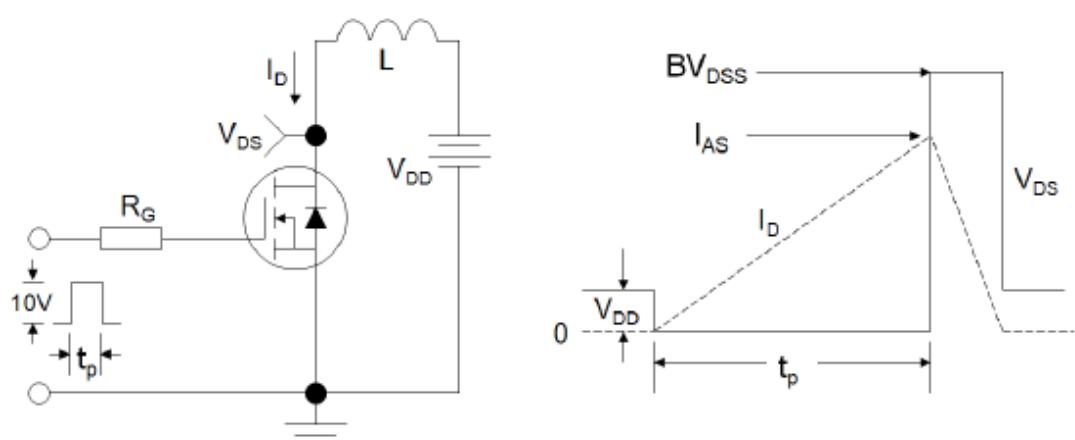




**Figure1:Gate Charge Test Circuit & Waveform**



**Figure 2: Resistive Switching Test Circuit & Waveforms**



**Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms**

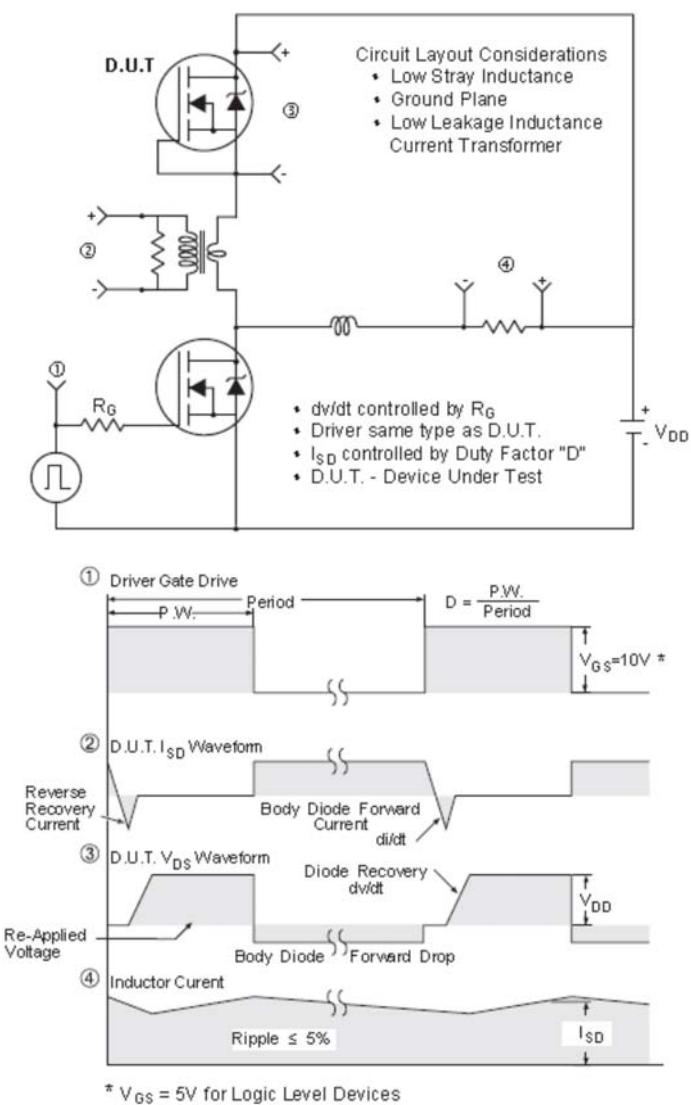
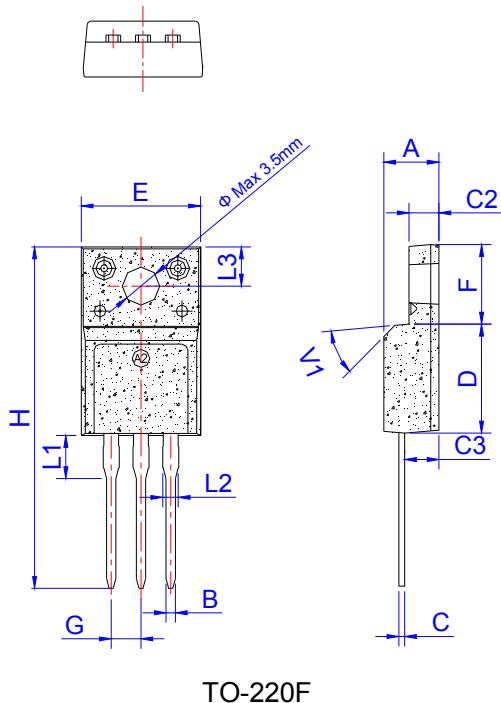


Figure 4:Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)

## Package Mechanical Data



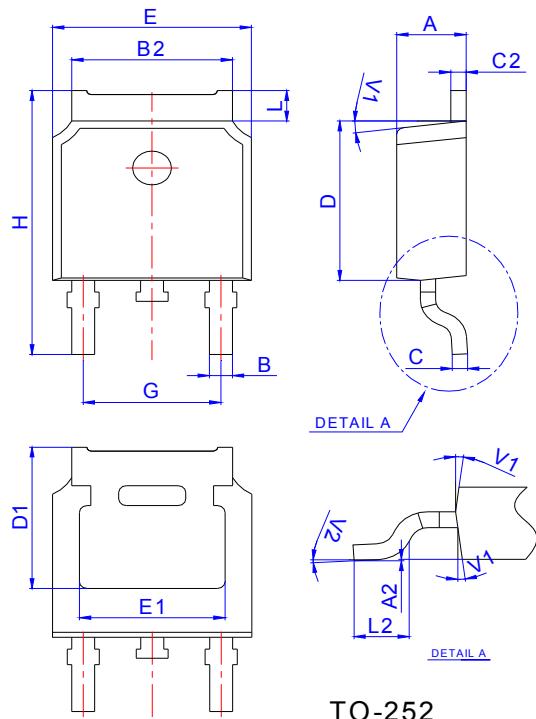
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

## **Package Information -TO-220F**

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000

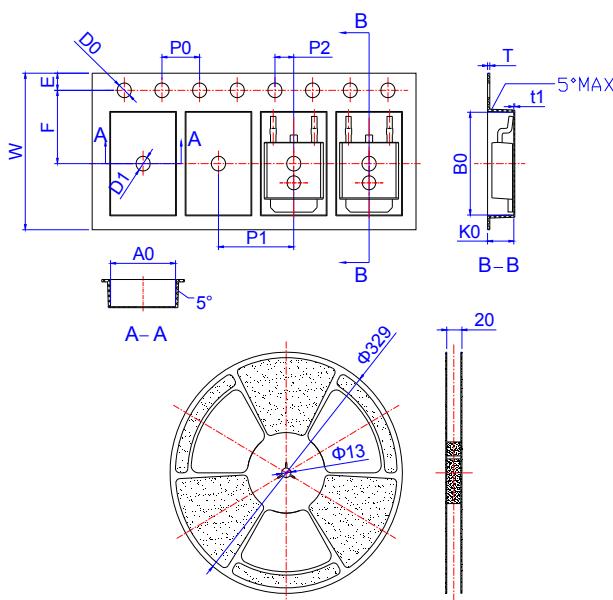


## Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

## Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TAPING	2,500	25,000	13inch



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